Drift-Diffusion model for spin-polarized electron transport in semiconductors

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- Motivation: need for future semiconductor devices
- Idea: exploit electron spin
- Main aim: analyze spin Drift-Diffusion model
- Starting point: paper Possanner-Negulescu, 2011

Model

 $N \in \mathbb{C}^{2 \times 2}$ - electron density, $J \in \mathbb{C}^{2 \times 2}$ - current, $\Omega \subset \mathbb{R}^3$ - domain.

$$\partial_t N + \operatorname{div} J + i\gamma [N, \vec{m} \cdot \vec{\sigma}] = \frac{1}{\tau} \left(\frac{1}{2} \operatorname{tr}(N) \sigma_0 - N \right),$$
 (1)

$$J = -DP^{-1/2} (\nabla N + N\nabla V) P^{-1/2},$$
 (2)

 $\gamma > 0$ - pseudo-exchange field, $\vec{m} \in \mathbb{R}^3$ - direction of magnetization, $\tau > 0$ - spin-flip relaxation time, D = D(x) > 0 - space-dependent diffusion coefficient, $\vec{\sigma} = (\sigma_1, \sigma_2, \sigma_3)$ - triple of the Pauli matrices, σ_0 - unit matrix in $\mathbb{C}^{2 \times 2}$, $P = \sigma_0 + p \vec{m} \cdot \vec{\sigma}$, where $p = p(x) \in [0, 1)$.

$$N = \frac{1}{2}n_D\sigma_0$$
 on $\partial\Omega$, $t > 0$, $N(0) = N^0$ in Ω . (3)

Poisson equation:

$$-\lambda_D^2 \Delta V = \operatorname{tr}(N) - C(x) \quad \text{in } \Omega, \quad V = V_{D_{\mathbb{P}}} \text{, on } \partial_{\Omega} \Omega.$$

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Main points

$$\begin{cases} \partial_t N + \operatorname{div} J + i\gamma [N, \vec{m} \cdot \vec{\sigma}] = \frac{1}{\tau} \left(\frac{1}{2} \operatorname{tr}(N) \sigma_0 - N \right), \quad (1) \\ J = -DP^{-1/2} (\nabla N + N\nabla V) P^{-1/2}, \quad (2) \quad + \operatorname{Poisson} \operatorname{eq} (4). \end{cases}$$

Difficulties:

- Nonlinearity due to $N\nabla V$
- Strong coupling due to matrix-valued variables
- NO analytical results: no maximal principle, no regularity theory, no L^∞ estimates

Main ideas and techniques:

- Different formulations help for decoupling
- Fixed point theorem, Stampacchia method, Moser-type iteration method

Charge and spin-vector densities formulation

<u>Reformulation I: Pauli basis</u> $N = \frac{1}{2}n_0\sigma_0 + \vec{n}\cdot\vec{\sigma}, J = \frac{1}{2}j_0\sigma_0 + \vec{j}\cdot\vec{\sigma}.$ n_0 - electron charge density, $\vec{n} = (n_1, n_2, n_3)$ - spin-vector density.

$$\begin{split} \partial_t n_0 &-\operatorname{div}\left(\frac{D}{\eta^2}(J_0 - 2p\vec{J}\cdot\vec{m})\right) = 0,\\ \partial_t n_k &-\operatorname{div}\left(\frac{D}{\eta^2}\left(\eta J_k + (1-\eta)(\vec{J}\cdot\vec{m})m_k - \frac{p}{2}J_0m_k\right)\right)\\ &-2\gamma(\vec{n}\times\vec{m})_k = -\frac{n_k}{\tau}, k = 1, 2, 3,\\ J_0 &= \nabla n_0 + n_0\nabla V, \ \vec{J} = \nabla \vec{n} + \vec{n}\nabla V, \ x \in \Omega, \ t > 0. \end{split}$$

Boundary and initial conditions:

$$n_0 = n_D, \ \vec{n} = 0 \text{ on } \partial \Omega, \ t > 0, \ n_0(0) = n_0^0, \ \vec{n}(0) = \vec{n}^0 \text{ in } \Omega,$$

Advantage: system of scalar equations

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Spin-up and spin-down densities formulation

Reformulation II: spin-up / spin-down densities $n_{\pm} = \frac{1}{2}n_0 \pm \vec{n} \cdot \vec{m}$

$$\partial_t n_+ - \operatorname{div} (D(1+p)(\nabla n_+ + n_+ \nabla V)) = rac{1}{2 au}(n_- - n_+), \ \partial_t n_- - \operatorname{div} (D(1-p)(\nabla n_- + n_- \nabla V)) = rac{1}{2 au}(n_+ - n_-).$$

Boundary and initial conditions:

$$n_{+} = n_{-} = \frac{1}{2}n_{D} \text{ on } \partial\Omega, \ t > 0, \ n_{\pm}(0) = \frac{1}{2}n_{0}^{0} \pm \vec{n}^{0} \cdot \vec{m} \text{ in } \Omega.$$

Advantage: decoupling, helps for boundedness proof

Parallel and perpendicular densities formulation

Reformulation III: parallel / perpendicular densities

$$egin{aligned} ec{n}_{\parallel} &= (ec{n}\cdotec{m})ec{m} ext{ and } ec{n}_{\perp} &= ec{n} - (ec{n}\cdotec{m})ec{m} : \ \partial_tec{n}_{\parallel} - ext{div}\left(rac{D}{\eta^2}igl((ec{J}\cdotec{m})ec{m} - rac{p}{2}J_0ec{m}igr)
ight) = -rac{ec{n}_{\parallel}}{ au}, \ \partial_tec{n}_{\perp} - ext{div}\left(rac{D}{\eta^2}(
abla ec{n}_{\perp} + ec{n}_{\perp}
abla V)
ight) + 2\gamma(ec{n}_{\perp} imes ec{m}) = -rac{ec{n}_{\perp}}{ au}. \end{aligned}$$

Advantage: equation for \vec{n}_\perp doesn't depend on $\vec{n}_\parallel,$ helps for boundedness proof

Theorem: Existence of bounded weak solutions

$$\begin{cases} \partial_t N + \operatorname{div} J + i\gamma [N, \vec{m} \cdot \vec{\sigma}] = \frac{1}{\tau} \left(\frac{1}{2} \operatorname{tr}(N) \sigma_0 - N \right), \quad (1) \\ J = -DP^{-1/2} (\nabla N + N\nabla V) P^{-1/2}, \quad (2) \quad + \operatorname{Poisson} \operatorname{eq}(4). \end{cases}$$

Theorem

Let T > 0, $\Omega \subset \mathbb{R}^3$ - bounded domain : $\partial \Omega \in C^{1,1}$. Let λ_D , γ , D > 0, 0 $0 < n_D \in H^1(\Omega) \cap L^{\infty}(\Omega), \quad V_D \in W^{2,q_0}(\Omega), \quad q_0 > 3,$ $n_0^0, \ \vec{n}^0 \cdot \vec{m}, \ |\vec{n}^0| \in L^\infty(\Omega), \quad \frac{1}{2}n_0^0 \pm \vec{n}^0 \cdot \vec{m} \ge 0.$ Then \exists a unique solution $(N = \frac{1}{2}n_0\sigma_0 + \vec{n}\cdot\vec{\sigma}, V)$ to (1) - (4) such that $n_0, n_k \in W^{1,2}(0, T; H^1_0, L^2), \quad V \in L^{\infty}(0, \infty; W^{2,q_0}(\Omega)), \quad q_0 > 3,$ $0 < n_0 \pm \vec{n} \cdot \vec{m} \in L^{\infty}(0, \infty; L^{\infty}(\Omega)), \quad |\vec{n}| \in L^{\infty}(0, T; L^{\infty}(\Omega))$

Scheme of the proof

$$\begin{cases} \partial_t n_+ - \operatorname{div} (D(1+p)(\nabla n_+ + n_+ \nabla V)) = \frac{1}{2\tau}(n_- - n_+), \\ \partial_t n_- - \operatorname{div} (D(1-p)(\nabla n_- + n_- \nabla V)) = \frac{1}{2\tau}(n_+ - n_-). \\ \partial_t \vec{n}_\perp - \operatorname{div} \left(\frac{D}{\eta^2} (\nabla \vec{n}_\perp + \vec{n}_\perp \nabla V) \right) + 2\gamma (\vec{n}_\perp \times \vec{m}) = -\frac{\vec{n}_\perp}{\tau}. \end{cases}$$

- Leray-Schauder for H^1 existence for (n_0, \vec{n})
- Boundedness
 - Stampacchia technique for L^{∞} bounds of $n_{\pm} = \frac{1}{2}n_0 \pm \vec{n} \cdot \vec{m}$ $\Rightarrow n_0, \vec{n} \cdot \vec{m} \in L^{\infty}(0, \infty; L^{\infty}(\Omega))$
 - **2** Moser-type iterations $(L^q \text{ estimates}, q \to \infty) \Rightarrow L^{\infty}$ bound for $\vec{n}_{\perp} \Rightarrow L^{\infty}$ bound for $\vec{n} = \vec{n}_{\perp} + (\vec{n} \cdot \vec{m})\vec{m}$



- Stationary 1D simulation
- Finite Volume Discretization
- Scharfetter-Gummel scheme

$$\begin{cases} x \in (0, x_1] : \vec{m} = 0, p(x) = 0, \\ x \in (x_1, x_2] : \vec{m} = \begin{pmatrix} 0 \\ 0 \\ 1 \end{pmatrix}, p(x) = p, \\ x \in (x_2, x_3] : \vec{m} = 0, p(x) = 0 \end{cases}$$

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Results: n₀ density

Electron density n0



- Discontinuity of derivative at interfaces
- Influence of magnetic field is stronger with increasing of p (spin polarization)

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Results: *n*₃ density

Electron density n3 0.2 0.1 n₃ density 0 -0.1-0.2 [•]∎-0.6 0.2 0.4 0.8 1.2 1 length, m $\cdot 10^{-6}$

• Gives distribution of spin vector density

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$$n_1 = n_2 = 0$$
 since $m_1 = m_2 = 0$

- Matrix drift-diffusion system for spin-coherent transport in semiconductors was investigated: existence, uniqueness and boundedness of the solution is proved
- Numerical solution for multilayered 1D semiconductor device was presented

Outlook

- Analysis for $\vec{m} \neq const$
- 2D simulation

Thank you!

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